
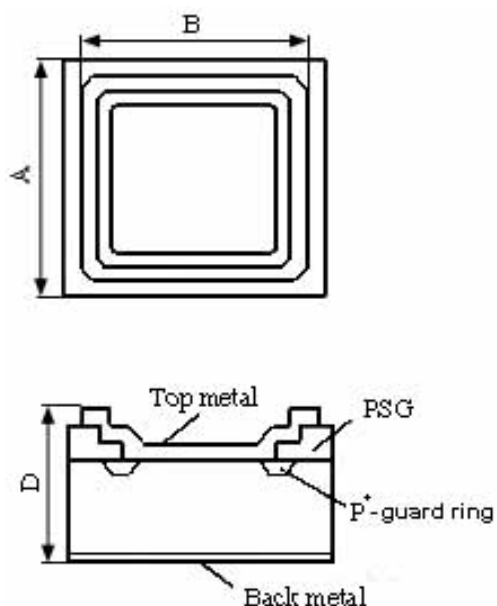


SCHOTTKY DIODES KDS 2128V. PRELIMINARY



Rev.1. Feb. 2010

|  VSP-MIKRON | 1A/15V. Die Size-51mil. | | | |
|---|--------------------------------|------------------------|-------------------|--------------------|
| Electrical Characteristics | Symbol | Unit | Spec. limit | Die Sort |
| Breakdown Voltage @ $I_R=10\text{mA}$ | V_{BR} | V | 18 | 20 |
| Average Rectified Forward Current | $I_{F(AV)}$ | A | 1,0 | - |
| DC Forward Voltage @ 25°C , $I_F=1,0\text{A}$ | V_F | V | 0,30 | 0,29 |
| Maximum Reverse Current @ 25°C , $V_R=15\text{V}$ 25°C , $V_R=18\text{V}$ 100°C , $V_R=15\text{V}$ | I_R | mA | 2,0 - 50,0 | 1,5 2,5 45,0 |
| Peak Forward Surge Current 8,3ms single half sine-wave superimposed on rated load (JEDEC METHOD) | I_{FSM} | A | 60 | - |
| Peak Repetitive Reverse Surge Current @ $2,0\mu\text{s}$, $f=1\text{kHz}$., $T_J<125^\circ\text{C}$. | I_{RRM} | A | 2,0 | |
| Electrostatic Discharge Voltage. JEDEC Method. ESD HBM. Contact. | ESD | kV | ± 8 (contact) | |
| Voltage Rate of Change | dV/dt | $\text{V}/\mu\text{S}$ | 10.000 | |
| Operating Junction Temperature | T_J | $^\circ\text{C}$ | 125 | |



| DIM | ITEM | μm |
|-------------------|---------------------|---------------|
| A_x A_y | Wafer Form Die Size | 1300 1300 |
| B_x B_y | Top Metal Size | 1112 1112 |
| D | Thickness | 300max. |
| Scribe line Width | | 80 |

Top metal: a) **Al** – for Wire Bonding;
b) **Al-Ni-Ag** – for Soldering.
Backside metal: **Ti-Ni-Ag**.